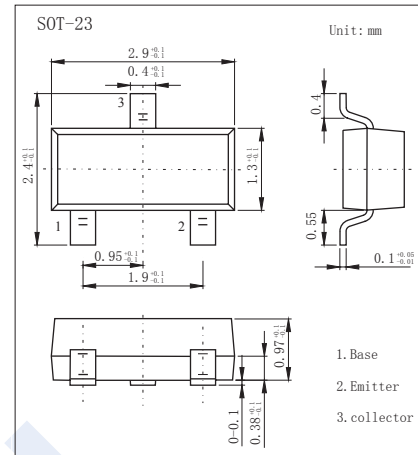


PNP Transistors

2SA1252

■ Features

- High V_{EBO} .
- Wide ASO and high durability against breakdown.
- Complementary to 2SC3134



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-15	V
Collector current	I_C	-150	mA
Collector current (pulse)	I_{CP}	-300	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-15			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -40 \text{ V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -10 \text{ V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 \text{ mA}$, $I_B = -5 \text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50 \text{ mA}$, $I_B = -5 \text{ mA}$			-1.2	
DC forward current gain	h_{FE}	$V_{CE} = -6 \text{ V}$, $I_C = -1 \text{ mA}$	90		600	
Collector output capacitance	C_{ob}	$V_{CB} = -6 \text{ V}$, $f = 1 \text{ MHz}$		3.5		pF
Transition frequency	f_T	$V_{CE} = -6 \text{ V}$, $I_C = -1 \text{ mA}$		100		MHz

■ Classification of h_{FE}

Type	2SA1252-D4	2SA1252-D5	2SA1252-D6	2SA1252-D7
Range	90-180	135-270	200-400	300-600
Marking	D4	D5	D6	D7

2SA1252

■ Typical Characteristics

